one conductivity type thereto with said channel forming region therebetween, and a pair of second regions in which a concentration of said impurity is smaller than that in said first regions wherein said second regions are interposed between said channel forming region and said pair of first regions,

wherein the pair of second regions are overlapped with the gate electrode of said thin film transistor.

Please add new claims 37-41 as follows:

--37. A semiconductor device comprising:

at least one first thin film transistor formed over a substrate;

a pixel electrode electrically connected to said first thin film transistor;

a driving circuit having at least one second thin film transistor formed over the substrate for driving first thin film transistor, each of said first and second thin film transistors comprising:

a gate electrode;

a gate insulating film adjacent to the gate electrode; and

a crystalline semiconductor film adjacent to said gate insulating film wherein said crystalline semiconductor film includes a channel forming region, a pair of first regions containing an impurity for giving one conductivity type thereto with said channel forming region therebetween, and a pair of second regions in which a concentration of said impurity is smaller than that in said first regions wherein said second regions are interposed between said channel forming region and said pair of first regions,

wherein the pair of second regions of said second thin film transistors are overlapped with the gate electrode of said second thin film transistor.

38. The semiconductor device according to claim 37 wherein said gate electrode is located over said crystalline semiconductor film in said first and second thin film transistors.